

Model Comparison

Model	VRRM VDRM(V)	ITAVIFAV(A)
C3PDB60N08	800	75
C3PDB60N12	1200	75
C3PDB60N14	1400	75
C3PDB60N16	1600	75
C3PDB60N18	1800	75

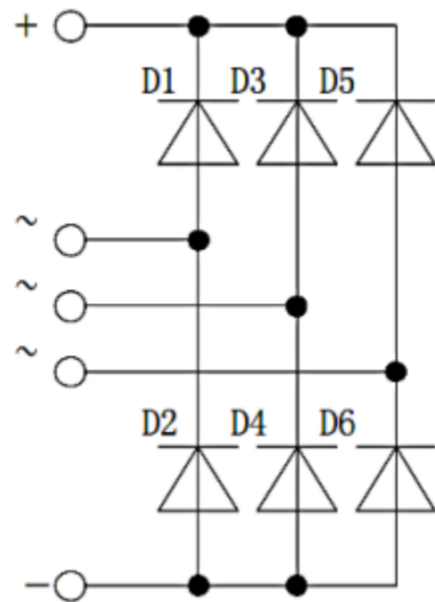
Features / Advantages

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications

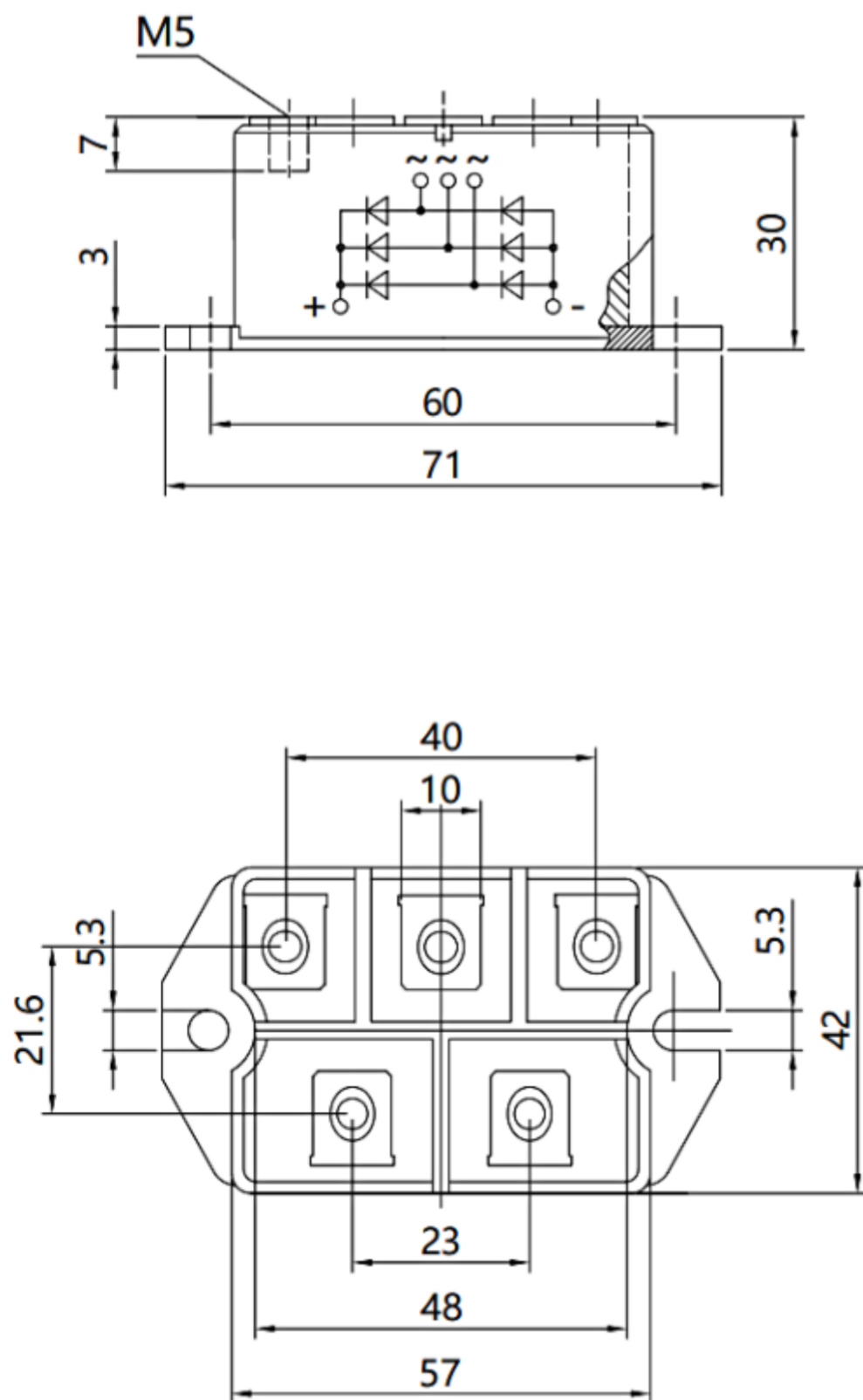
- Diode for main rectification
- For three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Internal Circuit



Package Dimension

Dimensions in Millimeters



Parameters

Parametrics	C3PDB60N08~18
V_{DRM} V_{RRM}	800~1800V
I_{dAV} @TC	75A
T_C	100°C
I_{FSM} 10ms, 45°C	550A

V_(F0) @Tvj max	0.78V
Package style Outline drawings	XEA